

IN THE CLAIMS

1-11 (Canceled Herein)

12. (Currently Amended) A method of determining a performance of plasma etch equipment, comprising the steps of

- providing a substrate having a film to be etched,
- etching the film using the plasma etch equipment,
- calculating an etch rate of the film during etching of the film,
- calculating a non-uniformity of the film during etching of the film,
- comparing the calculated data with predetermined data, and
- ~~deciding whether the performance of the plasma etch equipment is acceptable, on the basis of a result of comparing the calculated data with predetermined data~~ determining if the extracted data is within a specification.

13. (Original) The method according to claim 12, wherein the etch rate is calculated from interferometric endpoint (IEP) signals.

14. (Original) The method according to claim 12, wherein the etch rate is calculated from optical emission spectroscopy (OES) signals.

15. (Original) The method according to claim 12, wherein the non-uniformity is calculated from optical emission spectroscopy (OES) signals.

16-22. (Canceled Herein)